

Product Overview

NTMFS4C029N: Single N-Channel Power MOSFET 30 V, 46 A, 5.88mΩ

For complete documentation, see the data sheet.

Power MOSFET 30 V, 46 A, Single N-Channel, SO-8 FL

Features

- Low RDS(on) to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- RoHS Compliant

Applications

- CPU Power Delivery
- DC-DC Converters

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	V_{GS} Max (V)	$V_{GS}^{(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 10$ V (mΩ)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	C_{iss} Typ (pF)	Package Type
NTMFS4C029NT1G	0.15	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Single	30	20	2.2	46	0.69	-	9	5.88	15	18.9	987	SO-8FL / DFN-5
NTMFS4C029NT3G	0.2665	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Single	30	20	2.2	46	0.69	-	9	5.88	15	18.9	987	SO-8FL / DFN-5

For more information please contact your local sales support at www.onsemi.com.

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